

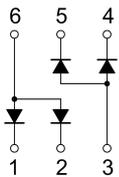
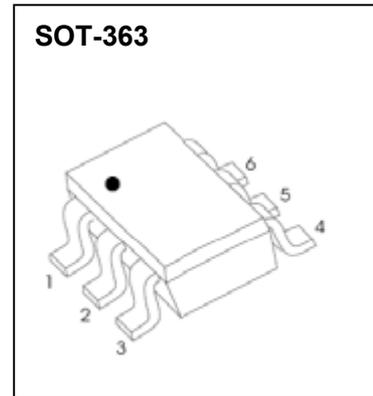
Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE ARRAYS

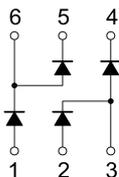
FEATURES

- Low Forward Voltage Drop
- Fast Switching
- Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version

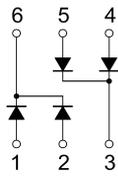
MARKING:



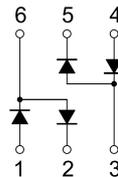
BAT54ADW



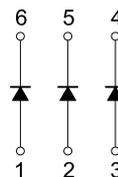
BAT54BRW



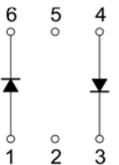
BAT54CDW



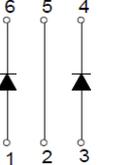
BAT54SDW



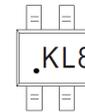
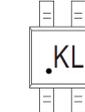
BAT54TW

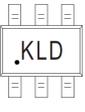


BAT54DW



BAT54JW

BAT54ADW	BAT54BRW	BAT54CDW	BAT54SDW	BAT54TW
				

BAT54DW	BAT54JW
	

Solid dot = Green molding compound device, if none, the normal device.

Solid dot = Pin1 indicate.

ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	30	V
V_{RWM}	Peak Working Reverse Voltage		
V_R	DC Blocking Voltage		
I_O	Forward Continuous Current	200	mA
I_{FRM}	Repetitive Peak Forward Current	300	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	600	
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	30			V
Reverse current	I_R	$V_R=25\text{V}$			2	μA
Forward voltage	V_F	$I_F=1\text{mA}$			320	mV
		$I_F=10\text{mA}$			400	
		$I_F=30\text{mA}$			500	
		$I_F=100\text{mA}$			1000	
Total capacitance	C_{tot}	$V_R=1\text{V}, f=1\text{MHz}$			15	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=0.1\times I_R, R_L=100\Omega$			5	ns

Typical Characteristics

